

GaAs Schottky Diode

Features

- Low Junction Capacitance
- typically 35 fF
- Low Series Resistance
- typically 6Ω
- Tri-metal system for improved reliability
- High cut-off frequency
- Polyimide passivation
- Durable Construction

Description

The HSCH-9401 is a discrete Schottky barrier diode fabricated with the Schottky Barrier Integrated Diode (SBID) process.

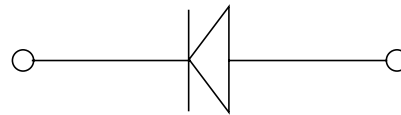
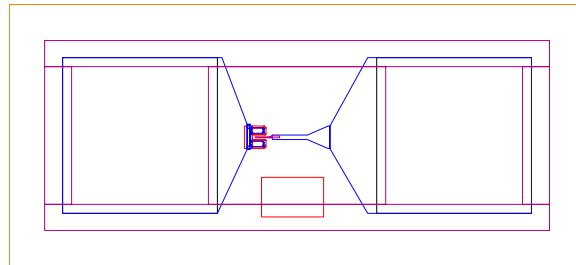
Applications

The HSCH-9401 is a general purpose millimeter wave diode that can be used as a detector or as a mixer in applications such as digital radio, LMDS, or video distribution.

Specifications

- V_f (1 mA): 630-800 mV
- V_f (10 mA): 730-980 mV
- R_s (5 mA): <8.5Ω
- B_v (-10 μA): >6V
- I_r (-2V): <200 nA
- C_t : <0.045 pF

HSCH-9401



Chip Size:	610 × 255 μm (24 × 10 mils)
Chip Size Tolerance:	± 10 μm (± 0.4 mils)
Chip Thickness:	100 μm (4 mils)
Chip Thickness Tolerance:	± 15 μm (± 0.6 mils)
Bond Pad Sizes:	175 × 175 μm (6.9 × 6.9 mils)

This data sheet contains a variety of typical and guaranteed performance data. The information supplied should not be interpreted as a complete list of circuit specifications. In this data sheet the term *typical* refers to the 50th percentile performance. For additional information contact your local HP sales representative.

Notes: